

SILICON TRANSISTOR 2SC3632-Z

NPN SILICON EPITAXIAL TRANSISTOR MP-3

DESCRIPTION

2SC3632-Z is designed for High Voltage Switching, especially in Hybrid Integrated Circuits.

FEATURES

- High Voltage VcEo = 600 V
- High Speed tr < 0.5 μs
- Complement to 2SA1413-Z

QUALITY GRADE

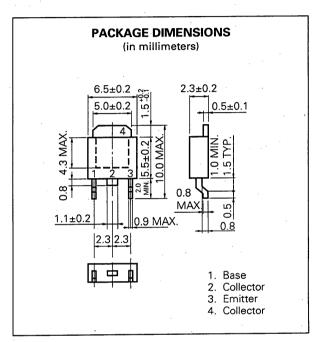
Standard

Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C)

Collector to Base Voltage	Vcво	600	٧
Collector to Emitter Voltage	Vceo	600	٧
Emitter to Base Voltage	Vево	7	٧
Collector Current (DC)	lc	1	Α
Collector Current (Pulse)*	Ic	2	Α
Total Power Dissipation (Ta = 25 °C)**	Рт	2.0	W
Junction Temperature	T_j	150	°C
Storage Temperature	Tstg	-55 to +150	°C

- * PW ≦ 10 ms, Duty Cycle ≦ 50 %
- ** When mounted on ceramic substrate of 7.5 cm² × 0.7 mm



ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

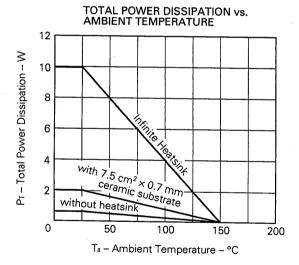
CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Collector Cutoff Current	Ісво			10	μΑ	VcB = 600 V, IE = 0
Emitter Cutoff Current	ІЕВО			10	μΑ	VEB = 7.0 V, Ic = 0
DC Current Gain	hFE1*	30	55	120		VcE = 5.0 V, lc = 100 mA
DC Current Gain	hFE2*	5	7			VcE = 5.0 V, Ic = 500 mA
Collector Saturation Voltage	VCE(sat)*		0.35	1.0	V	Ic = 400 mA, IB = 80 mA
Base Saturation Voltage	VBE(sat)*		0.9	1.2	V	Ic = 400 mA, IB = 80 mA
Gain Bandwidth Product	fτ		30		MHz	Vce = 5.0 V, Ie = -50 mA
Output Capacitance	Соь	·	14		pF	VcB = 10 V, IE = 0, f = 1.0 MHz
Turn-on Time	ton		0.1	0.5	μs	Ic = 0.5 A, R _L = 500 Ω
Storage Time	tstg		4.0	5.0	μs	IB1 = -IB2 = 0.1 A
Fall Time	tf		0.2	0.5	μs	Vcc = 250 V

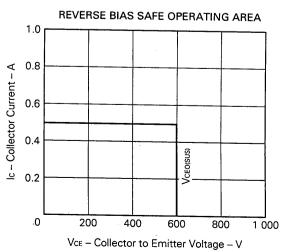
^{*} Pulsed: PW \leq 350 μ s, Duty Cycle \leq 2 %

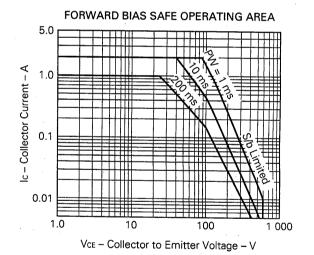
hre Classification

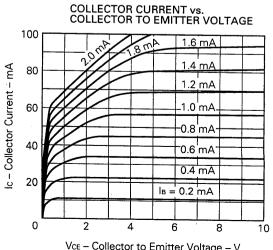
MARKING	М	L	К
hFE1	30 to 60	40 to 80	60 to 120

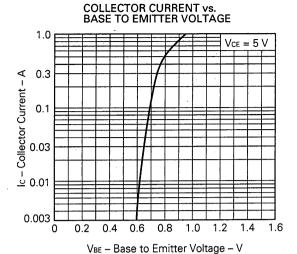
TYPICAL CHARACTERISTICS (Ta = 25 °C)

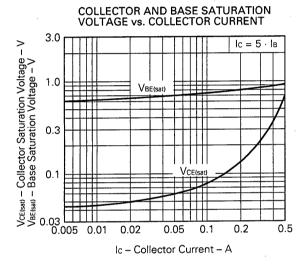


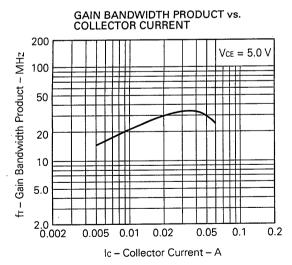


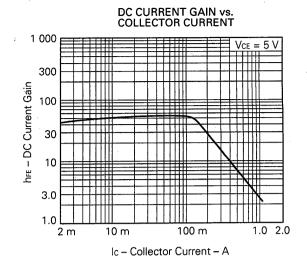


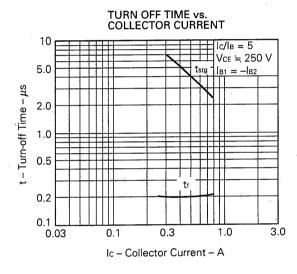


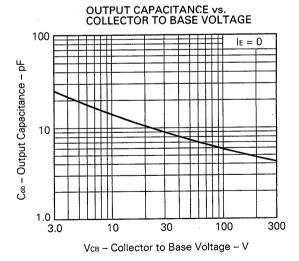


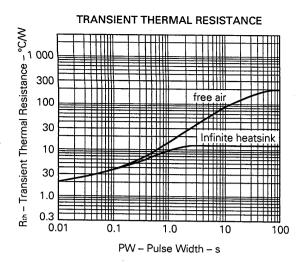












Reference

Application note name	No.
Quality control of NEC semiconductors devices.	TEI-1202
Quality control guide of semiconductors devices.	MEI-1202
Assembly manual of semiconductors devices.	IEI-1207
Design of Push-Pull Type Switching Regulators (Basic)	TEB-1002
Design of Push-Pull Type Switching Regulators (Applications)	TEB-1003
Optimum Base Drive Conditions of Switching Power Transistors	TEB-1014

[MEMO]

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Application examples recommended by NEC Corporation.

Standard: Computer, Office equipment, Communication equipment, Test and Measurement equipment, Machine tools, Industrial robots, Audio and Visual equipment, Other consumer products, etc.

Special: Automotive and Transportation equipment, Traffic control systems, Antidisaster systems, Anticrime systems, etc.

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